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# EP R&D WP5

## extension proposal

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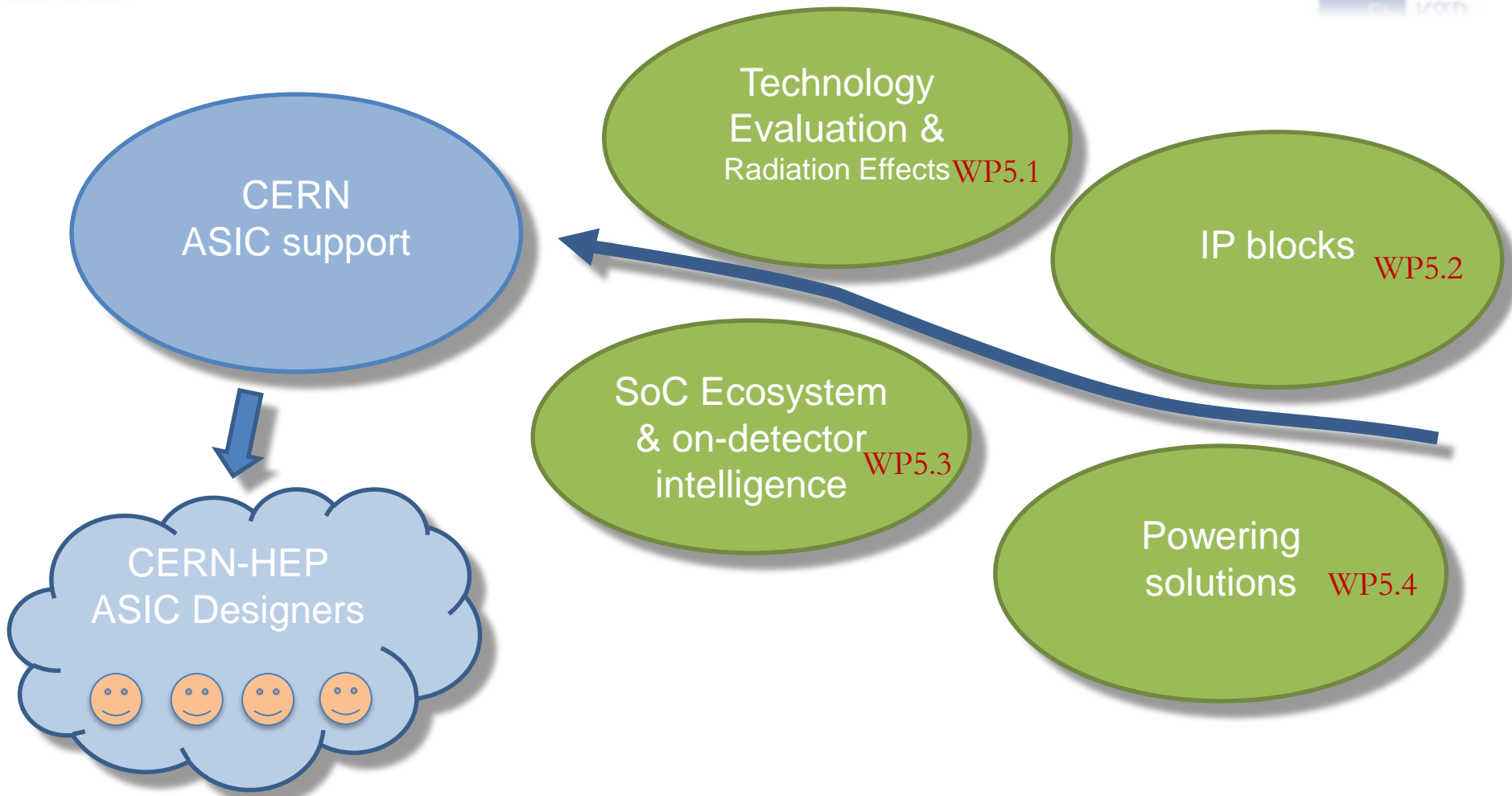
CERN EP R&D Day 2023

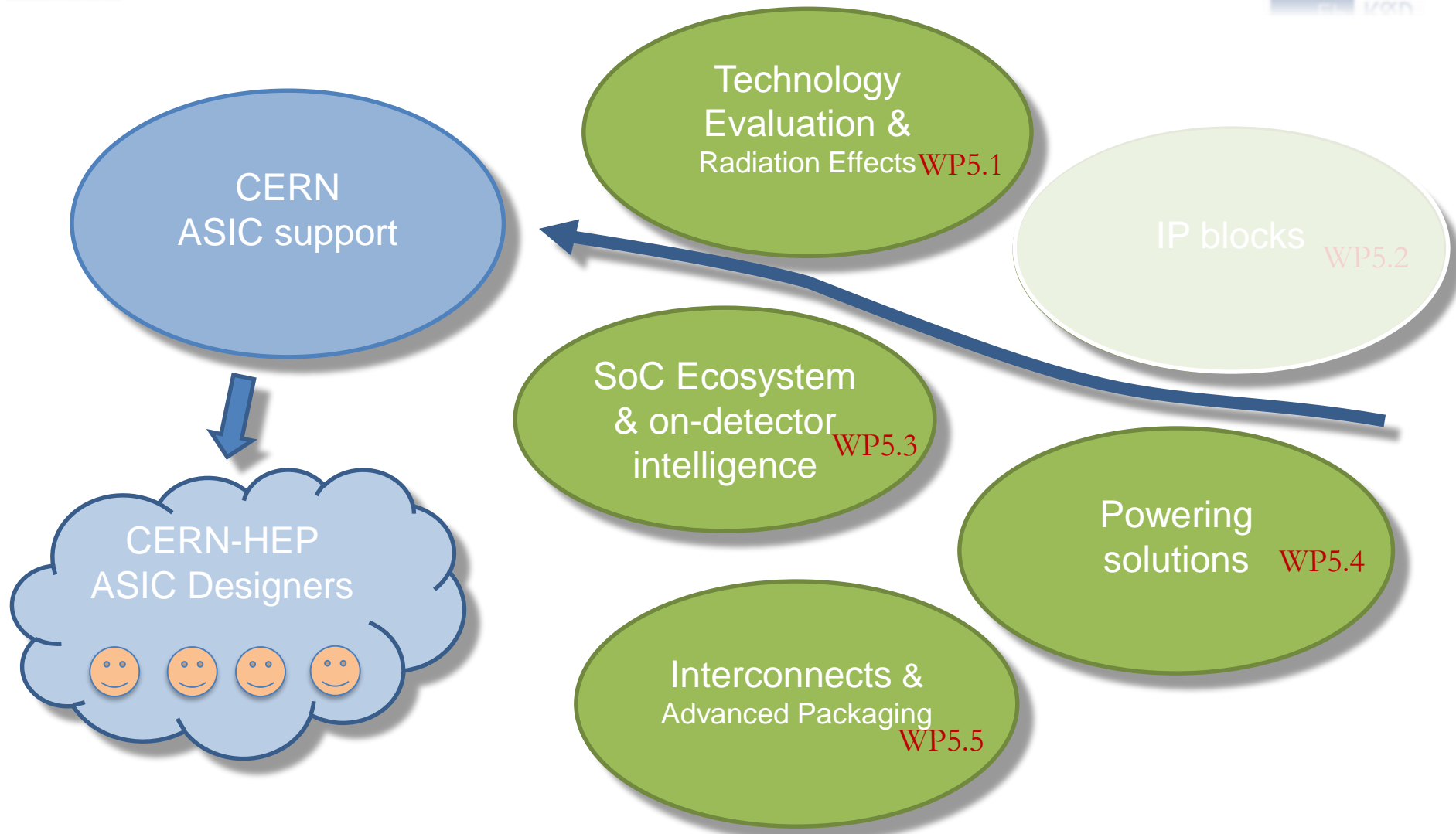
20 February 2023

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Davide Ceresa

on behalf of the EP R&D WP5





- Technology survey and evaluation
  - Maintain activity but at a slower pace
  
  - Advanced processes; access and evaluation
    - FinFET (radiation evaluation)
    - FD-SOI (non Rad-Tol applications)
      - Collaborating with external institute
  
  - Specialty Technologies; evaluation, customized developments
    - RRAM
    - MRAM
    - Ultra low leakage SRAM

Budget request: 120 kCHF  
Recourses request

(FTE)	Fellows	Students
year 1	0	1
year 2	0	1
year 3	0	1
year 4	0	1
year 5	0	0



- Rad-Tol IP blocks on 28nm bulk CMOS technology
  - Expect to complete and deliver all IP blocks by 2024-25
  - Maintain IP block repository by CERN ASIC support service
  - No further IP block development is foreseen within the EP R&D WP5
  - HEP community is invited to contribute with IP blocks

Budget request:  
Recourses request

(FTE)	Fellows	Students
year 1	0	0
year 2	0	0
year 3	0	0
year 4	0	0
year 5	0	0

## TWO COMPLEMENTARY R&D ACTIVITIES:



- STANDARDIZED SOLUTION
- OPEN SOURCE
- FULLY RADIATION TOLERANT
- ECO SYSTEM OPEN TO HELP THE COMMUNITY
  - RT SOC IP BLOCKS
  - RT SOC INTERCONNECT

Stand alone applications  
of Control & Monitoring

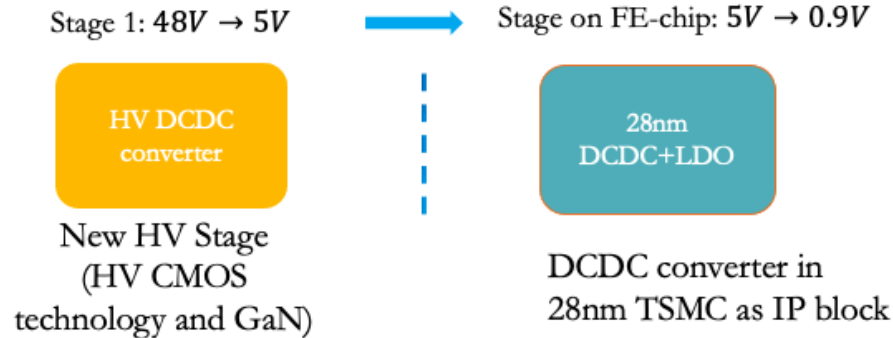


- APPLICATION SPECIFIC INSTRUCTION SET PROCESSOR
- COMMERCIAL TOOL – ASIP DESIGNER BY SYNOPSIS
- CUSTOM ISA
- CUSTOM MICROARCHITECTURE

IP blocks to support  
the implementation of  
Data Processing applications

Budget request: 500 kCHF  
Recourses request

(FTE)	Fellows	Students
year 1	1	2
year 2	2	3
year 3	2	3
year 4	2	3
year 5	1	1



Slide by: S. Michelis

## Stage 1: 48V → 5V

Find a new CMOS HV technology (old one no longer available)  
Explore the new upcoming GaN commercial technologies

} Full radiation characterization (TID, DD, SEE)

Find a suitable architecture for this high conversion ratio with main specification low volume, low noise, high efficiency, higher radiation hardness (bPOL48 only rated up to 5e14 n/cm<sup>2</sup>)

Power module design: provide to the experiment a small and optimized “brick” with all active and passive elements included.

## Stage 2: 5V → 0.9V

Continue the recently started R&D activity to:

- reach production readiness
- improve the design for a modular approach where designers can easily connect blocks for higher output current (>3A)
- design a linear regulator from 5V → 0.9V - 1.2V necessary for some I/O pads
- explore derived topologies for higher output voltages

Budget request: 340 kCHF  
Recourses request

(FTE)	Fellows	Students
year 1	0	0
year 2	1.5	0
year 3	2	0
year 4	2	0
year 5	1	0

## Advanced packaging & 3D Interconnects

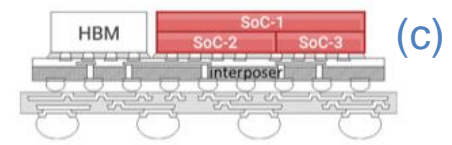
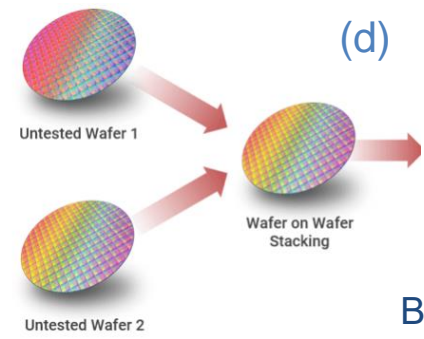
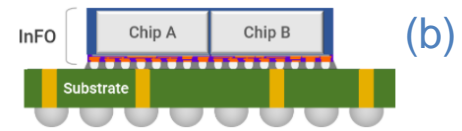
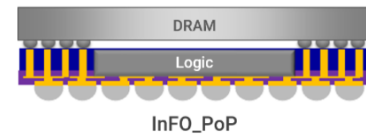
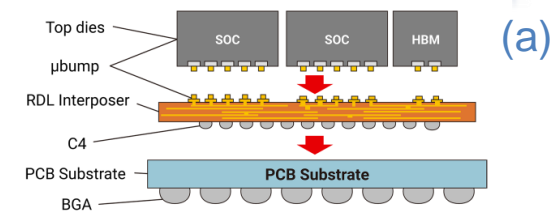
- Technology survey, access and evaluation
  - Silicon Interposer (a)
  - Wafer Level Packaging & TSVs (b)
  - Chip on Wafer (c)
  - Wafer on Wafer (d)

## Enabler for many applications

- Hybrid detectors
- Si Photonics

## Timeline

- Phase A
  - Identify industrial collaborators
  - Comparison between the 'third-party' and 'turn-key' approaches
- Phase B
  - Invest R&D funds to test the viability of the technologies
  - Test vehicle ASICs (ex. TimePix4)



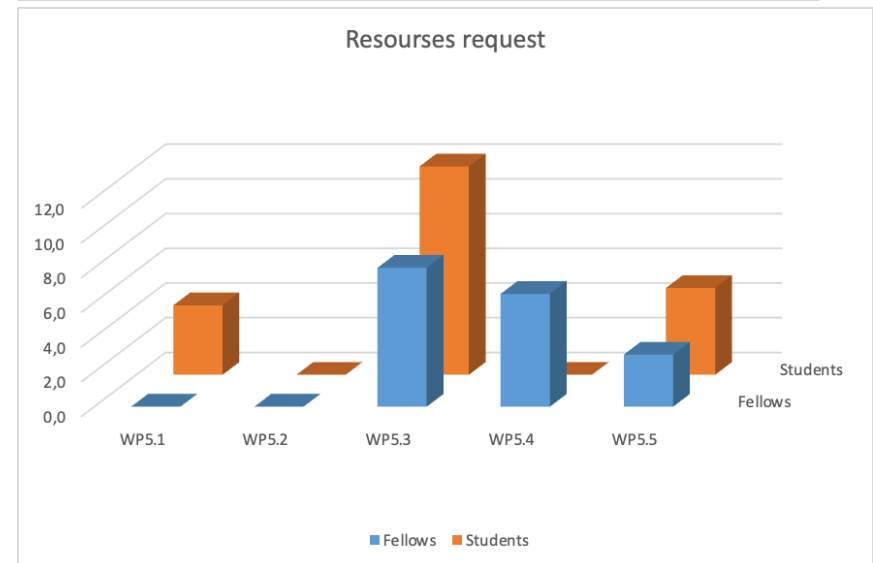
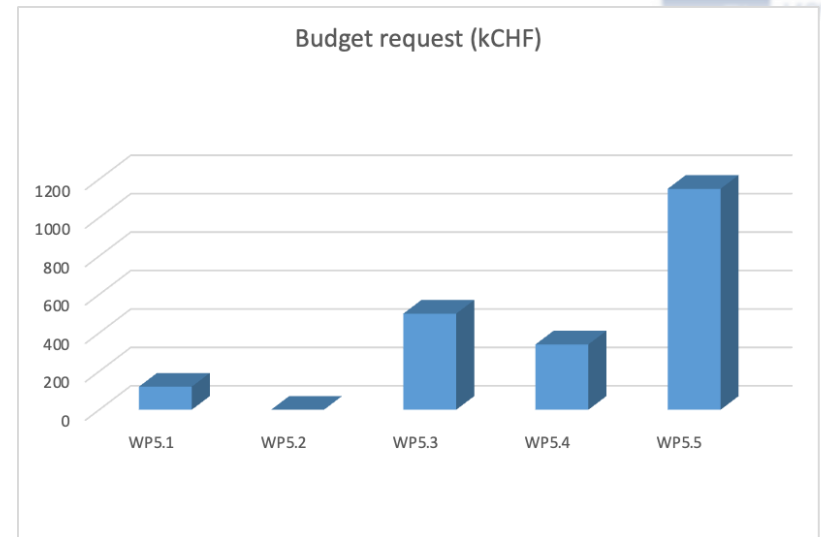
Budget request: 1'150 kCHF  
Recourses request

(FTE)	Fellows	Students
year 1	0	1
year 2	1	1
year 3	1	1
year 4	1	1
year 5	0	1



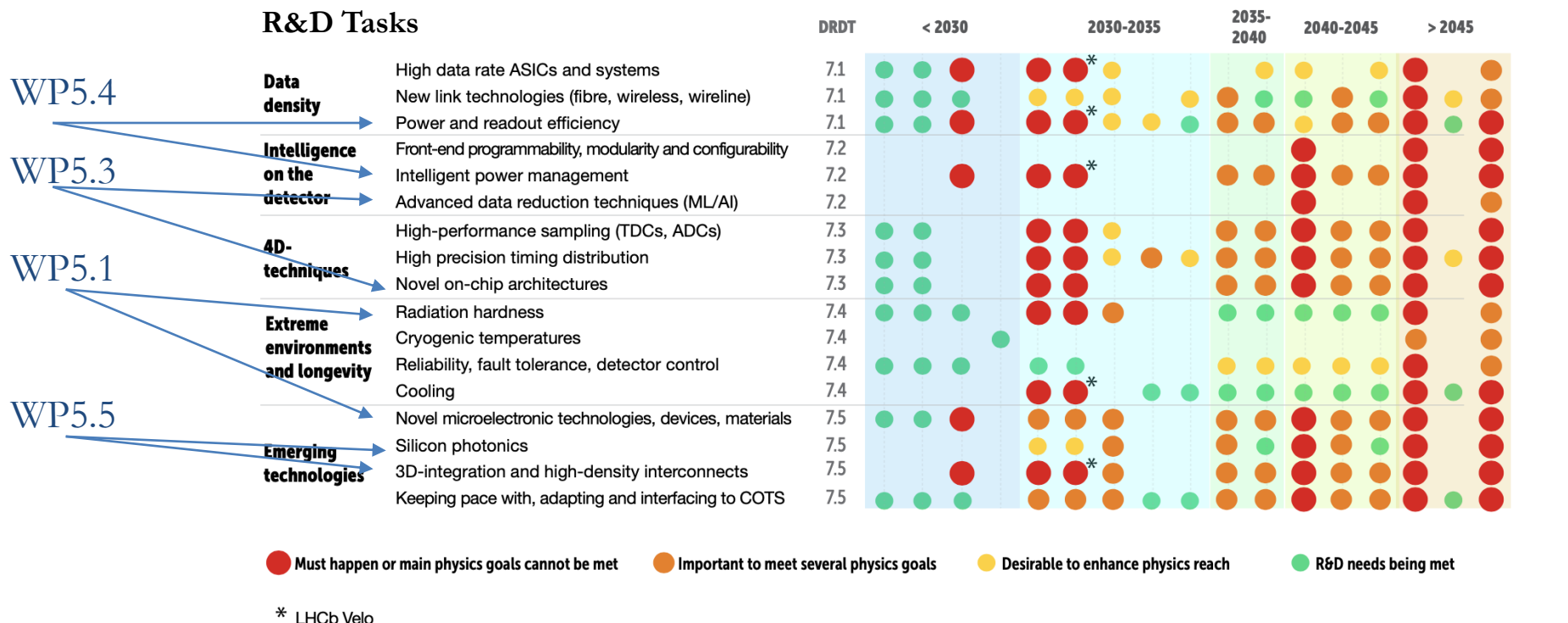
- Total Budget: 2,110 kCHF
- Total Recourses (2024-28)
  - Fellows: 16,5 (17,5)\*
  - Students: 17 (21)\*

*\* including 2024 top up*



## 2021 ECFA DETECTOR RESEARCH AND DEVELOPMENT ROADMAP Chapter 7 Electronics and Data Processing

EP R&D WP5 provides enablers for next generation experiments



● Must happen or main physics goals cannot be met   ● Important to meet several physics goals   ● Desirable to enhance physics reach   ● R&D needs being met

\* LHCb Velo

- Technology Choice
  - The selection and adoption of the 28nm CMOS technology as a “mainstream” process will “fuel” the developments of “near-future” experiments
  - “Further-future” collider experiments would require more advanced technologies offering the necessary combination of performance, power efficiency and radiation hardness
    - R&D on future state-of-the-art IC technologies would be necessary
- Infrastructure and Organizational issues
  - Common Design Platforms & Collaborative Framework
- ASICs evolution and front-end “intelligence”
  - Data processing adaptable to changing experimental conditions
  - Programmability to facilitate retargeting ASIC blocks to different applications
  - Present R&D on core-based SoC design topologies and methodologies will be applicable in “near-future” experiments as well as **pave the way** for the electronics of “further-future” colliders
- Power distribution
  - Staged voltage conversion, multiple supply voltages, intelligent power management
- Advanced packaging and 3D interconnects
  - Emerging technologies in industry providing enablers in many applications for HEP detectors

A nighttime photograph of the ATLAS detector dome at CERN, illuminated from within, set against a dark blue sky with stars and a meteor streak.

**Thank You**

- System-on-Chip Radiation Tolerant Ecosystem (SoCRaTEs)
  - Rad-Tol open-source Risc-V based core & interconnect infrastructure
  - Rad-Tol peripherals
  - Rad-Tol embedded FPGA (eFPGA); commercial or open-source based
  - Rad-Tol non-volatile memories (NV-RAM); commercial or open-source based
  
- Control & Monitoring applications
  - Rad-Tol Microcontroller style implementations
  
- On-Detector data processing applications
  - Modeling & Simulation
    - Simulation Framework development; Front-End to Back-End
  - Application Specific Implementations
    - Rad-Tol processing Cores
    - Rad-Tol Network on Chip
    - Rad-Tol Neural Networks
  
- Radiation Tolerance evaluation of SoC components

